PRODUCT NAME : BF421 PNP High Voltage Transistor (Pack of 5)

PRICE : Rs 39.00
SKU : RM1780

DESCRIPTION

Features

- Collector-Emitter Volt (Vceo): 300V
- Collector Current (Ic): 0.5A
- hfe: 50 @ 25mA
- Power Dissipation (Ptot): 625mW
- Current-Gain-Bandwidth (ftotal): 60MHz
- Type: PNP

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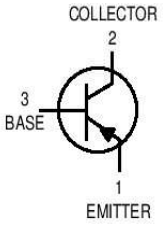
SEMICONDUCTOR TECHNICAL DATA

Order this document
by BF421/D

High Voltage Transistors
PNP Silicon

BF421
BF423



CASE 29–04, STYLE 14
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	BF421	BF423	Unit
Collector–Emitter Voltage	V_{CEO}	–300	–250	Vdc
Collector–Base Voltage	V_{CBO}	–300	–250	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0		Vdc
Collector Current — Continuous	I_C	–500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (1) (I_C = –1.0 mAdc, I_B = 0)	BF421 BF423	$V_{(BR)CEO}$	 –300 –250	 — —	Vdc
Collector–Base Breakdown Voltage (I_C = –100 μAdc, I_E = 0)	BF421 BF423	$V_{(BR)CBO}$	 –300 –250	 — —	Vdc
Emitter–Base Breakdown Voltage (I_E = –100 μAdc, I_C = 0)	BF421 BF423	$V_{(BR)EBO}$	 –5.0 –5.0	 — —	Vdc
Collector Cutoff Current (V_{CB} = –200 Vdc, I_E = 0)	BF421 BF423	I_{CBO}	 — —	 –0.01 —	μAdc
Emitter Cutoff Current (V_{EB} = –5.0 Vdc, I_C = 0)	BF421 BF423	I_{EBO}	 — —	 –100 —	nAdc

1. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

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